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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/676,295	09/30/2003	Andrea Urban	10191/3212A	8189
26646	7590	02/22/2007	EXAMINER	
KENYON & KENYON LLP ONE BROADWAY • NEW YORK, NY 10004			AHMED, SHAMIM	
ART UNIT		PAPER NUMBER		
				1765
SHORTENED STATUTORY PERIOD OF RESPONSE		MAIL DATE	DELIVERY MODE	
3 MONTHS		02/22/2007	PAPER	

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

Office Action Summary	Application No.	Applicant(s)
	10/676,295	URBAN ET AL.
Examiner	Art Unit	
Shamim Ahmed	1765	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1) Responsive to communication(s) filed on 24 November 2006.

2a) This action is **FINAL**. 2b) This action is non-final.

3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4) Claim(s) 1-8 and 10-21 is/are pending in the application.
4a) Of the above claim(s) _____ is/are withdrawn from consideration.

5) Claim(s) _____ is/are allowed.

6) Claim(s) 1-8,10-21 is/are rejected.

7) Claim(s) _____ is/are objected to.

8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9) The specification is objected to by the Examiner.

10) The drawing(s) filed on _____ is/are: a) accepted or b) objected to by the Examiner.

Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) All b) Some * c) None of:
1. Certified copies of the priority documents have been received.
2. Certified copies of the priority documents have been received in Application No. _____.
3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) Notice of References Cited (PTO-892) 4) Interview Summary (PTO-413)
2) Notice of Draftsperson's Patent Drawing Review (PTO-948) Paper No(s)/Mail Date. ____ .
3) Information Disclosure Statement(s) (PTO/SB/08)
Paper No(s)/Mail Date . 5) Notice of Informal Patent Application
6) Other: ____ .

DETAILED ACTION

Response to Arguments

1. Applicant's arguments with respect to claims 1-8, 10-21 have been considered but are moot in view of the new ground(s) of rejection.

Claim Rejections - 35 USC § 112

2. The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

3. Claims 2-3 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

4. Regarding claim 2, lines 5-6, the phrase "a high-frequency pulsed, low-frequency modulated high-frequency power is injected" renders the claim indefinite because it appears that the injecting the high-frequency -----power into the etching body contradicts the limitation of "refraining from injecting a high-frequency power" in claim 1 as claim 2 depends on claim 1.

Claim Rejections - 35 USC § 102

5. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

6. Claims 1-8, 10 and 18-20 are rejected under 35 U.S.C. 102(b) as being anticipated by Laermer (DE 199 57 169A).

In the following, the USP 6,926,844 is used as true translation of the reference DE 199 57 169A).

Laermer teaches an etching process for a silicon body using a plasma comprises coupling a high frequency pulsed high frequency power with the etching body by means of applied high frequency alternating voltage, wherein the power is further modulated with a low frequency at least temporarily, which inherently reads on the claimed limitation of "at least approximately ambipolar plasma" (see the abstract, col.5, lines 30-col.6, line 25).

Laermer teaches that the low frequency modulation preferably in the range of 50-1000Hz (col.4, lines 10-25) and the plasma is pulsed at a frequency of 10kHz to 500kHz (col.4, lines 47-49)

Laermer also teaches that the plasma is modulated with time and the intensity of the plasma is modulated between a maximum value and a minimum value (see figures 1a-1c).

Claim Rejections - 35 USC § 103

7. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

8. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein

were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

9. Claims 11-15 are rejected under 35 U.S.C. 103(a) as being unpatentable over Laermer et al (DE 199 57 169A) in view of Koshimizu (5,290,383).

Laermer et al discusses above in the paragraph 6 but fail to teach adding an inert gas in the plasma.

However, in a controlled plasma etching process of silicon substrate, Koshimizu teaches the addition of inert gas into the plasma in order to stabilize the plasma (col.14, lines 29-41).

Therefore, it would have been obvious to one of ordinary skilled in the art at the time of claimed invention to combine Koshimizu's teaching into Laermer et al's process for stabilizing the plasma as taught by Koshimizu.

10. Claims 16-17 are rejected under 35 U.S.C. 103(a) as being unpatentable over Laermer et al (DE 199 57 169A) in view of Hashimoto et al (5,779,925).

Laermer et al discusses above in the paragraph 6 but fail to teach synchronizing the modulation and the low-frequency modulation with one another.

However, Hashimoto et al teach that the RF bias is synchronized with the on/off modulation in order to reduce charging damage without lowering the throughput (col.16, lines 35-42, lines 66-col.17, line 5).

Therefore, it would have been obvious to one of ordinary skill in the art at the time of claimed invention to combine Hashimoto et al's teaching into Laermer et al's process for reducing charging damage and for improved etching precision as taught by Hashimoto et al.

11. Claim 21 is rejected under 35 U.S.C. 103(a) as being unpatentable over Laermer et al (DE 199 57 169A) in view of Dockrey (4,799,991).

Laermer et al discusses above in the paragraph 6 but fail to teach that the under etching is performed using highly oxidizing fluorine compound includes ClF_3 .

However, in a process of silicon etching, Dockrey teaches both the NF_3 and ClF_3 can be used as an efficient etchant for silicon (see claims 7 and 12).

Therefore, it would have been obvious to one of ordinary skilled in the art at the time of claimed invention to combine Dockrey's teaching into Laermer et al's process because both NF_3 and ClF_3 are functionally equivalent as taught by Dockrey, as Laermer uses fluorocarbon gas (NF_3).

Conclusion

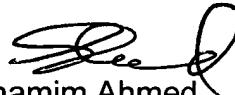
The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Wolf, Stanley illustrates conventional etcher that does not inject high-frequency power after attaining plasma that inherently includes ambipolar plasma; Kamata et al (6,060,329) illustrates that high-frequency is lowered to suppress electron density in the plasma zone because the loss of electrons by the ambipolar diffusion is suppressed (col.3, liens 8-12).

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Shamim Ahmed whose telephone number is (571) 272-1457. The examiner can normally be reached on M-Thu (7:00-5:30) Every Friday Off.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine G. Norton can be reached on (571) 272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Art Unit: 1765

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.



Shamim Ahmed
Primary Examiner
Art Unit 1765

SA

February 19, 2007